1200V Super-Junction Power MOSFET

DESCRIPTION

1200V Super-junction Power MOSFET

The 1200V High Voltage Super-junction power MOSFET is a customized technology developed based on common 1200V Super-junction MOSFETs platform，designed by Wuxi Unigroup Microelectronics Company. The 1200V High Voltage Super-junction power MOSFET provide an extremely low switching, communication and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler.

FEATURES

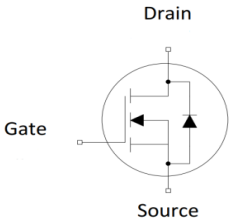
- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

TO-220F

TO-263



Device Marking and Package Information

Device	Package	Marking
TPA120R1K5A	TO-220F	120R1K5A
TPB120R1K5A	TO-263	120R1K5A

Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	1200	V
$R_{DS(on),max}$	1.5	Ω
$Q_{g,typ}$	32.75	nC
I_D	7	A
$I_{D,pulse}$	21	A
E_{OSS} @ 400V	2.47	μJ
Body Diode di_F/dt	50	A/μs

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted				
Parameter		**Symbol**	**Value**	**Unit**
Drain-Source Voltage (V_{GS} = 0V)		V_{DSS}	1200	V
Continuous Drain Current	T_C = 25ºC	I_D	7	A
	T_C = 100ºC		4	
Pulsed Drain Current (note1)		$I_{D,pulse}$	21	A
Gate-Source Voltage		V_{GSS}	±30	V
Single Pulse Avalanche Energy (note2)		E_{AS}	588	mJ
Avalanche Current		I_{AS}	7	A
Power Dissipation For TO-220F		P_D	34	
Power Dissipation For TO-263			151	W
Continuous Body Diode Current		I_S	7	A
Pulsed Diode Forward Current (note1)		I_{SM}	21	
MOSFET dv/dt ruggedness, V_{DS} = 0...650V		dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS} = 0…650V, $I_{SD} \le I_D$		dv/dt	5	A/us
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	ºC

Thermal Resistance TO-220F			
Parameter	**Symbol**	**Value**	**Unit**
Thermal Resistance, Junction-to-Case	R_{thJC}	3.9	ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

Thermal Resistance TO-263			
Parameter	**Symbol**	**Value**	**Unit**
Thermal Resistance, Junction-to-Case	R_{thJC}	0.83	ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

Specifications T_J = 25ºC, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	1200	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 1200V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
		V_{DS} = 1200V, V_{GS} = 0V, T_J = 150ºC	--	--	100	
Gate-Source Leakage	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5	--	4.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 3.5A	--	1.3	1.5	Ω
Forward Transconductance (Note3)	g_{fs}	V_{DS} = 20V, I_D = 3.5A	--	7	--	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1.0MHz	--	1349	--	pF
Output Capacitance	C_{oss}		--	55	--	
Reverse Transfer Capacitance	C_{rss}		--	3.09	--	
Total Gate Charge	Q_g	V_{DD} = 520V, I_D = 7A, V_{GS} = 10V	--	32.75	--	nC
Gate-Source Charge	Q_{gs}		--	7.5	--	
Gate-Drain Charge	Q_{gd}		--	11.5	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 400V, I_D = 7A, R_G = 25Ω	--	48	--	ns
Turn-on Rise Time	t_r		--	66	--	
Turn-off Delay Time	$t_{d(off)}$		--	140	--	
Turn-off Fall Time	t_f		--	44	--	
Drain-Source Body Diode Characteristics						
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 7A, V_{GS} = 0V	--	0.86	1.2	V
Reverse Recovery Time	t_{rr}	V_R = 400V, I_F = I_S , di_F/dt = 100A/μs	--	506	--	ns
Reverse Recovery Charge	Q_{rr}		--	5	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	18.7	--	A

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 1%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

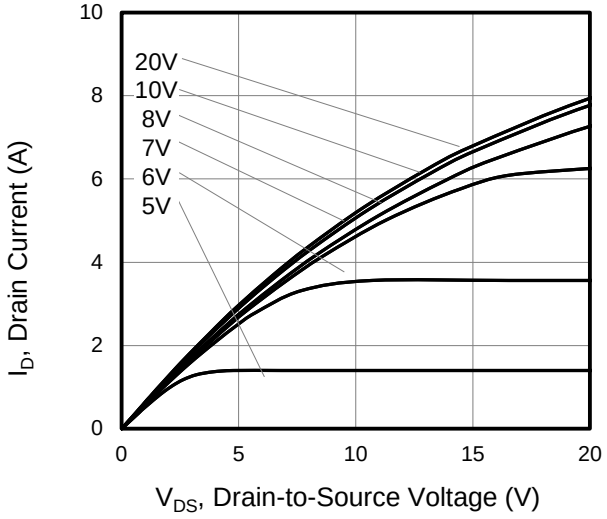


Figure 2. Transfer Characteristics

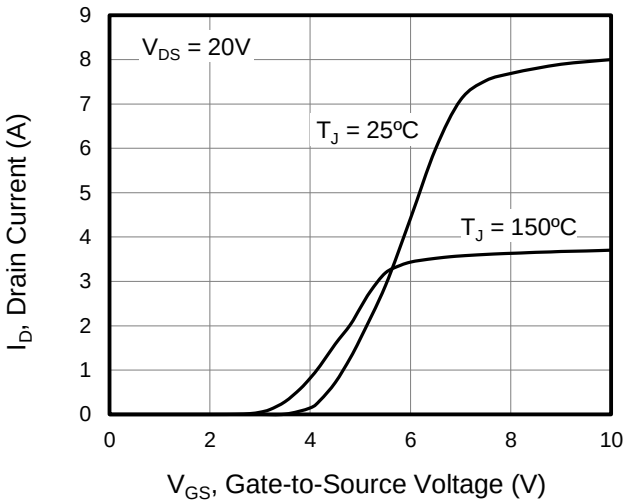


Figure 3 . On-Resistance vs. Drain Current

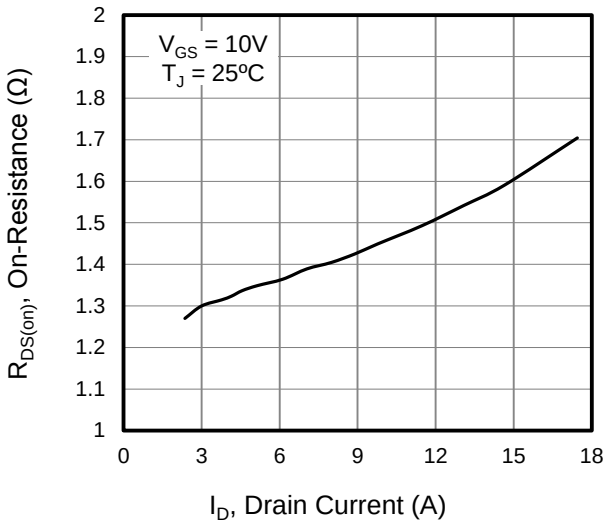


Figure 4. Capacitance

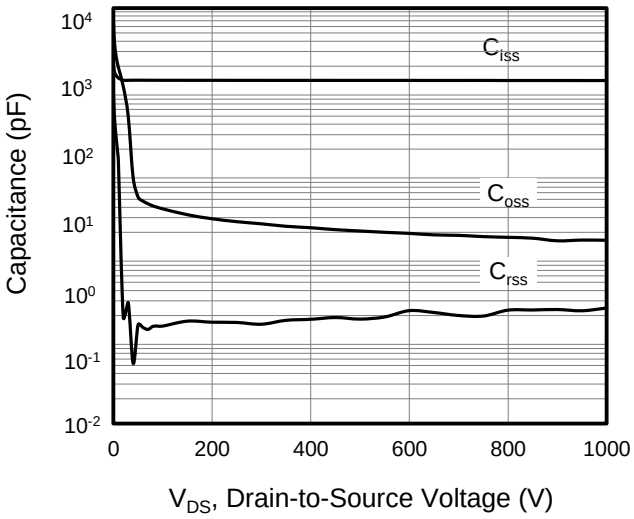


Figure 5. Gate Charge

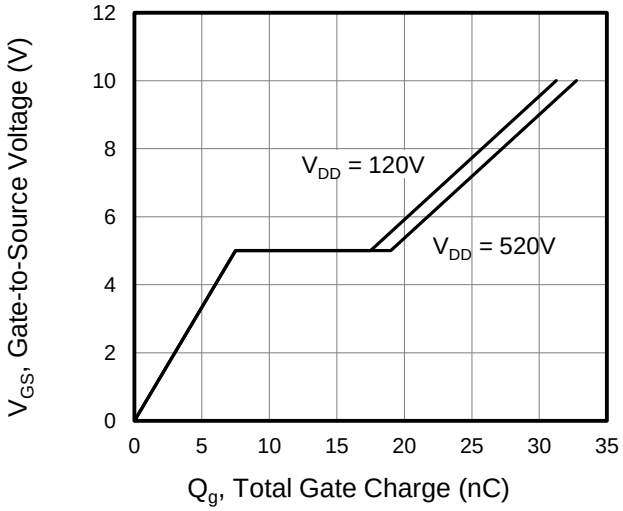
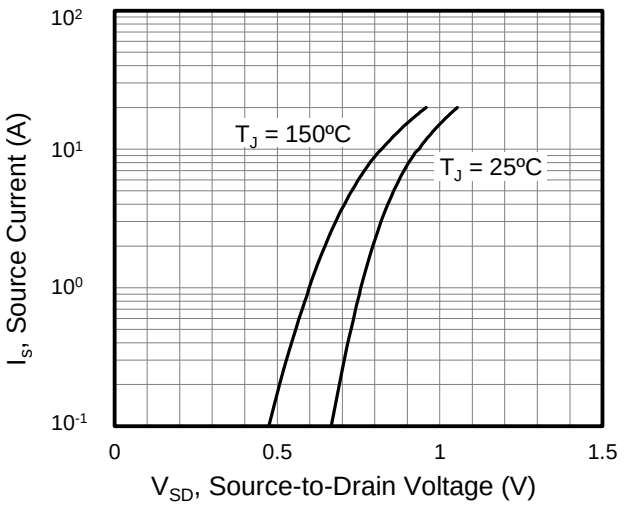


Figure 6. Body Diode Forward Voltage



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Breakdown voltage vs. Junction Temperature

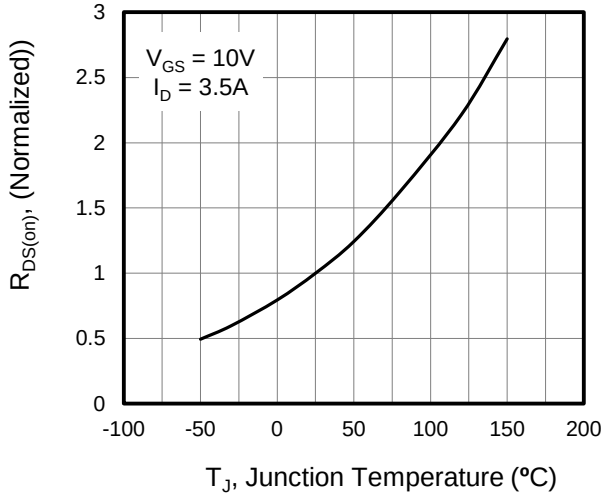


Figure 8. Threshold Voltage vs. Junction Temperature

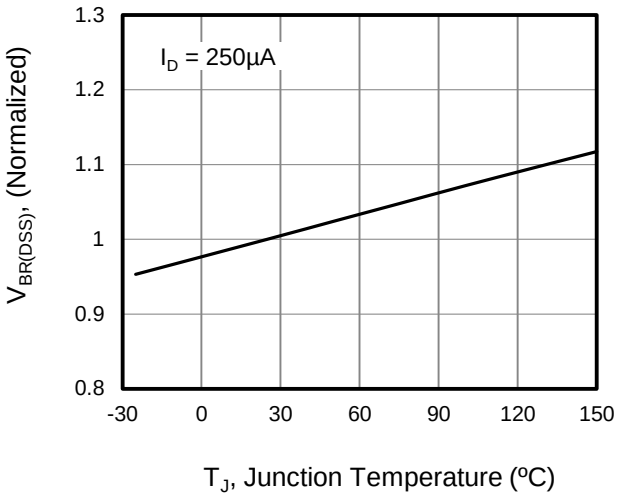


Figure 9. Transient Thermal Impedance TO-220F

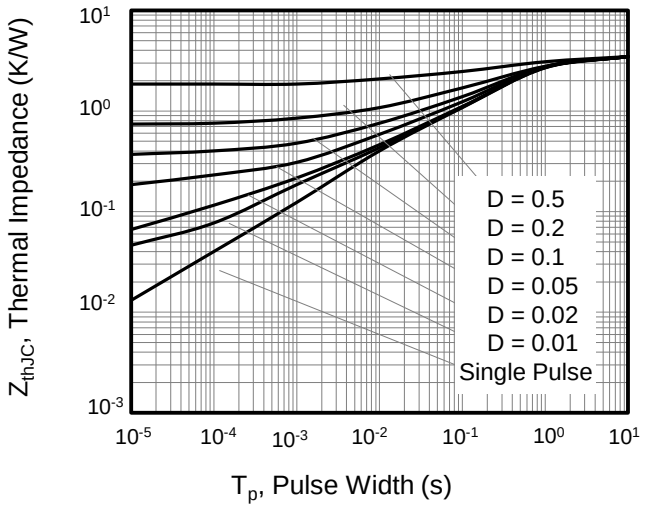


Figure 10. Transient Thermal Impedance TO-263

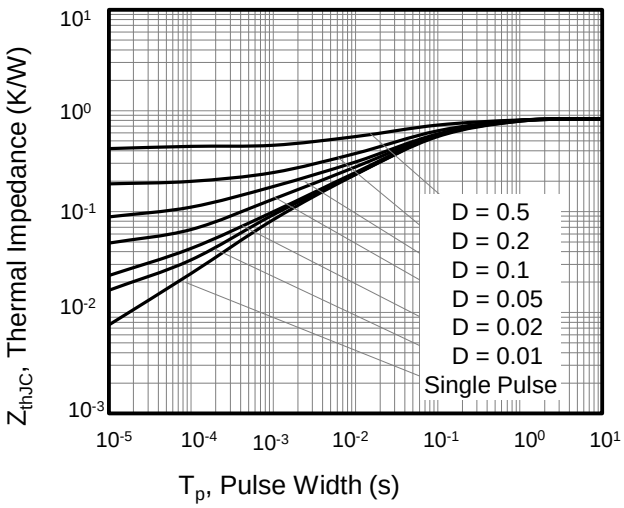


Figure 11. Safe operation area for TO-220F

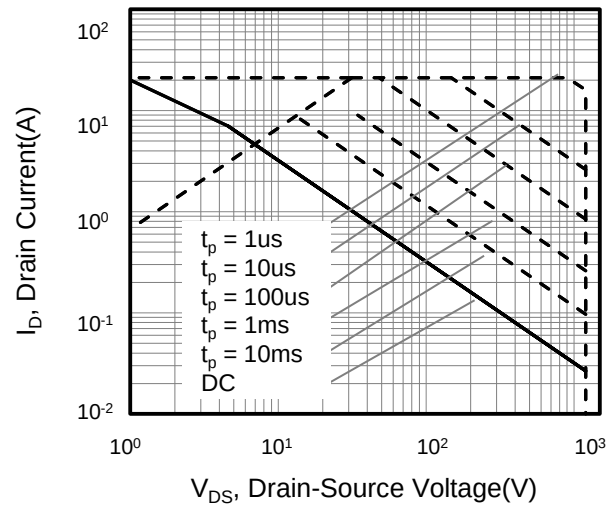
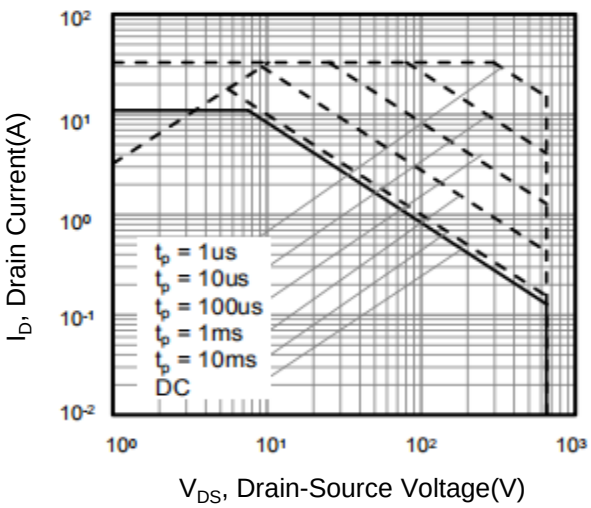


Figure 12. Safe operation area for TO-263



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 13. Typ. Coss Stored Energy

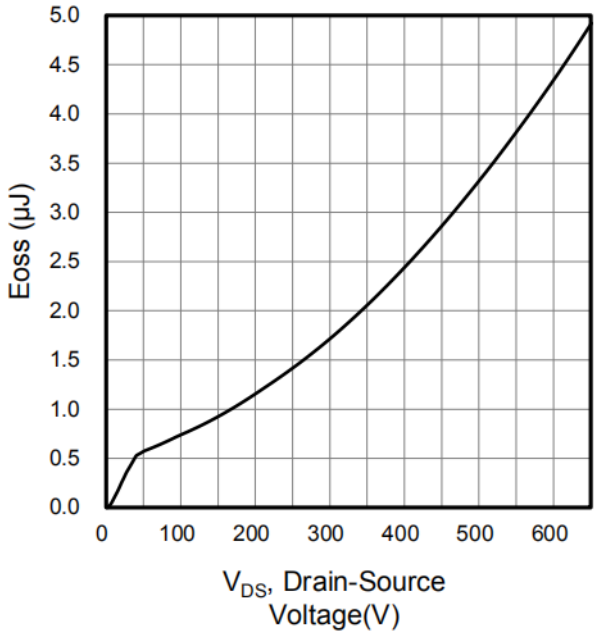


Figure A：Gate Charge Test Circuit and Waveform

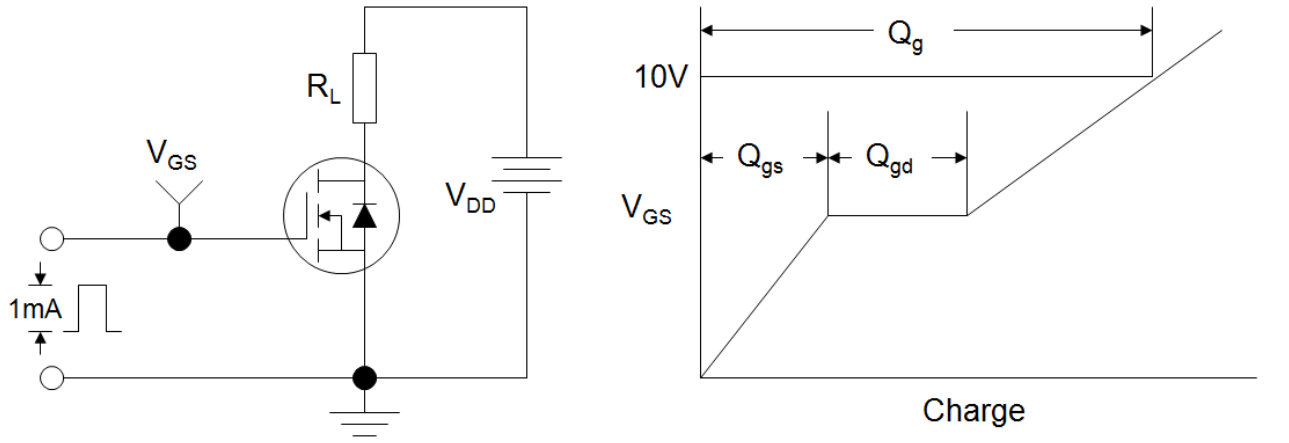


Figure B：Resistive Switching Test Circuit and Waveform

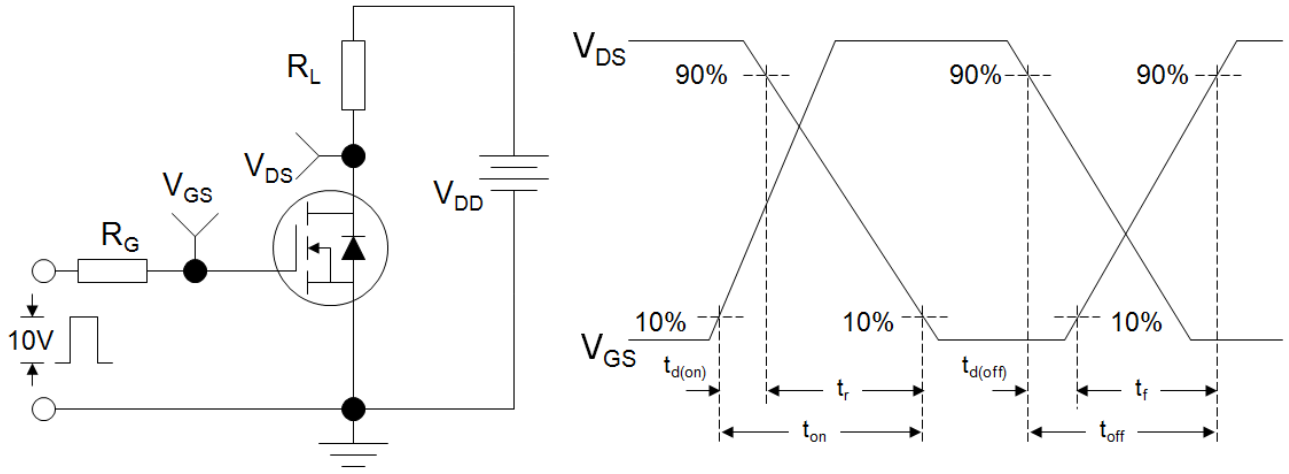
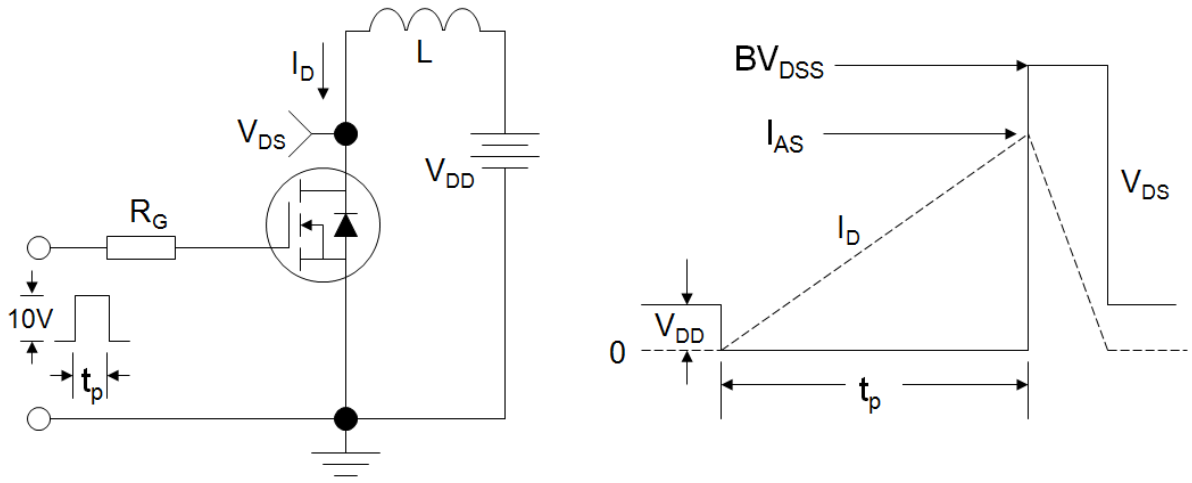
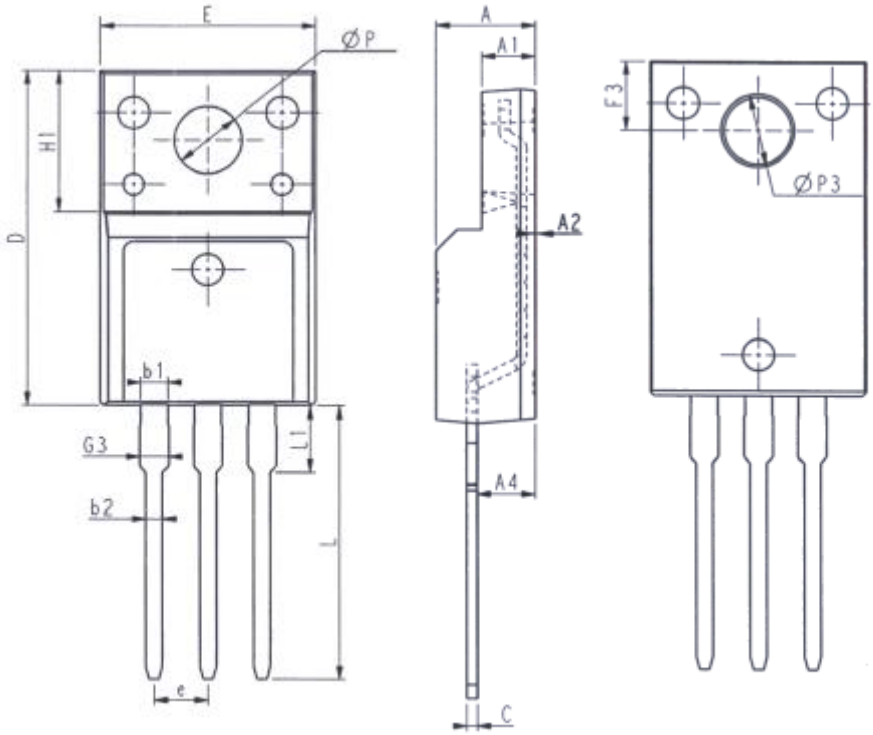


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



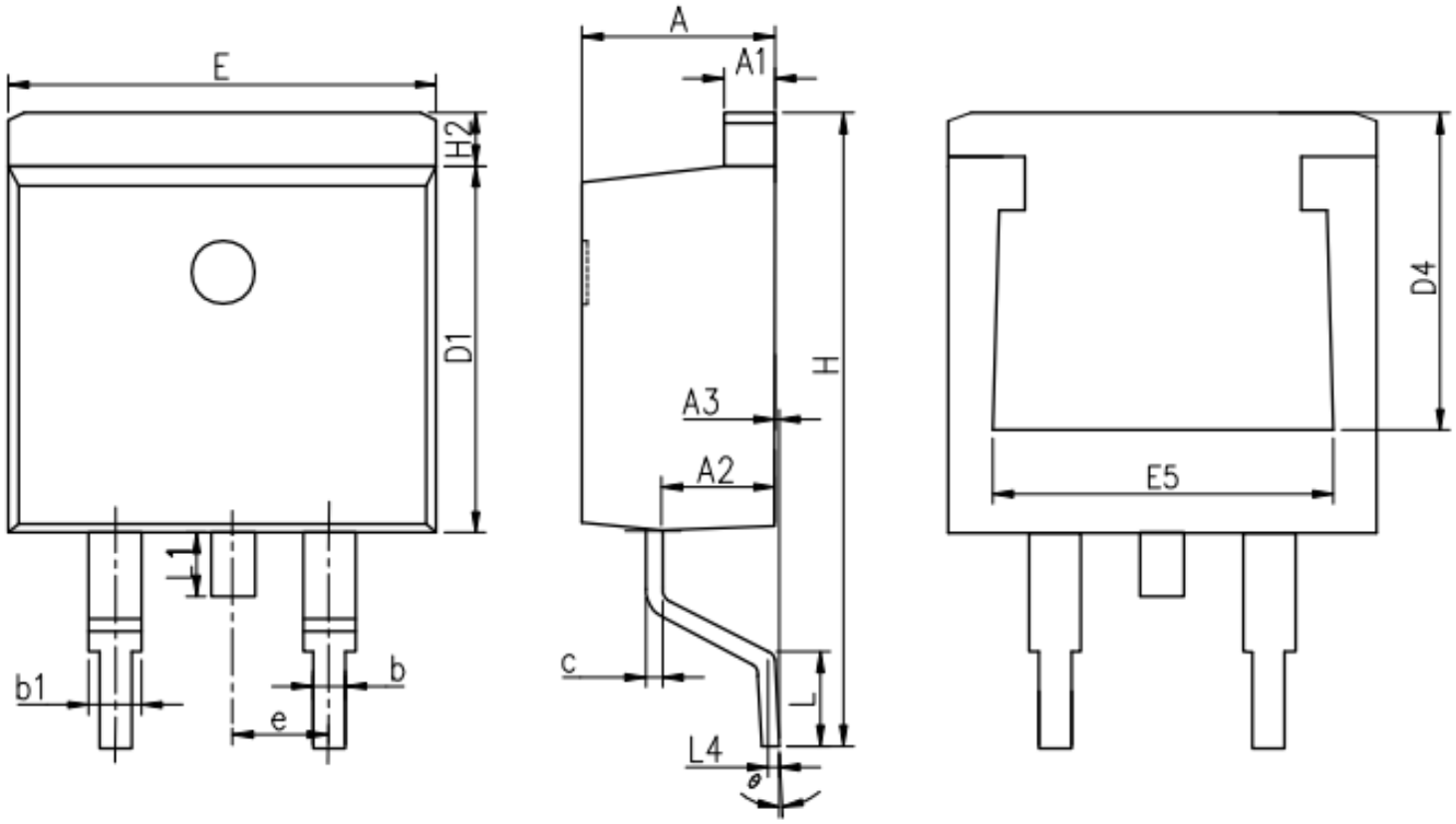
TO-220F



Unit: mm		
Symbol	Min.	Max.
E	9.96	10.36
A	4.50	4.90
A1	2.34	2.74
A2	0.30	0.60
A4	2.56	2.96
c	0.40	0.65
D	15.57	16.17
H1	6.70REF	
e	2.54BSC	

Unit: mm		
Symbol	Min.	Max.
L	12.68	13.28
L1	2.93	3.13
P	3.03	3.38
P3	3.15	3.65
F3	3.15	3.45
G3	1.25	1.55
b1	1.18	1.43
b2	0.70	0.95

TO-263



Unit:mm			
Symbol	**Min.**	**Nom**	**Max.**
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0.00	0.13	0.25
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
c	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	-	-

Unit:mm			
Symbol	**Min.**	**Nom**	**Max.**
E	9.86	10.16	10.36
E5	7.06	-	-
e	2.54BSC		
H	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.30	2.60
L1	1.40	1.55	1.70
L4	0.25BSC		
θ	0°	5°	9°

Disclaimer

All product specifications and data are subject to change without notice.

For documents and material available from this datasheet, Wuxi Unigroup does not warrant or assume any legal liability or responsibility for the accuracy, completeness of any product or technology disclosed hereunder.

No license, express or implied, by estoppels or otherwise, to any intellectual property rights is granted by this document or by any conduct of Wuxi Unigroup.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling Wuxi Unigroup products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Wuxi Unigroup for any damages arising or resulting from such use or sale.

Wuxi Unigroup disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Wuxi Unigroup's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

Wuxi Unigroup Microelectronics CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

In the event that any or all Wuxi Unigroup products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

Information (including circuit diagrams and circuit parameters) herein is for example only. It is not guaranteed for volume production. Wuxi Unigroup believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.